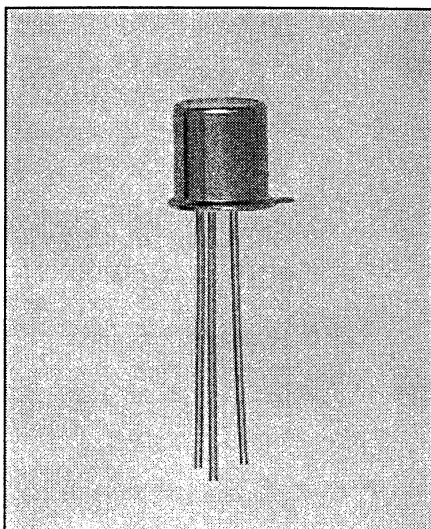
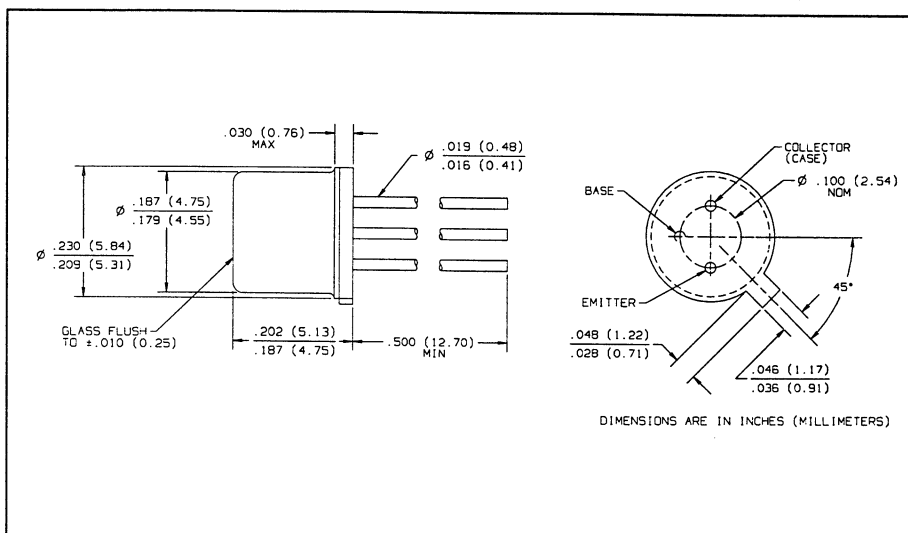


# NPN Silicon Photodarlington Type OP830WSL



## Features

- Wide receiving angle
- Enhanced temperature range
- Excellent thermal characteristics
- TO-18 hermetically sealed package
- Mechanically and spectrally matched to the OP130W and OP231W series of infrared emitting diodes

## Description

The OP830WSL consists of an NPN silicon photodarlington mounted in a hermetically sealed package. The wide receiving angle provides relatively even reception over a large area.

Photodarlington devices are normally used in applications where light signal levels are low and more current gain is needed than is possible with phototransistors. TO-18 packages offer high power dissipation and superior hostile environment operation.

## Replaces

OP830W and K9030 series

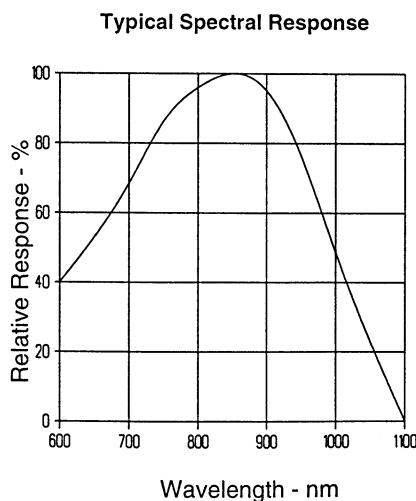
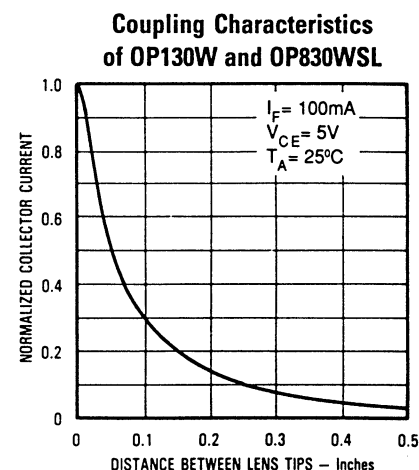
## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

|                                                                                          |                                             |
|------------------------------------------------------------------------------------------|---------------------------------------------|
| Collector-Emitter Voltage                                                                | 15 V                                        |
| Emitter-Collector Voltage                                                                | 5 V                                         |
| Continuous Collector Current                                                             | 50 mA                                       |
| Storage Temperature Range                                                                | $-65^\circ\text{C}$ to $+150^\circ\text{C}$ |
| Operating Temperature Range                                                              | $-55^\circ\text{C}$ to $+125^\circ\text{C}$ |
| Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron] | $260^\circ\text{C}^{(1)}$                   |
| Power Dissipation                                                                        | $250\text{ mW}^{(2)}$                       |

### Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering.
- (2) Derate linearly  $2.5\text{ mW}/^\circ\text{C}$  above  $25^\circ\text{C}$ .
- (3) Junction temperature maintained at  $25^\circ\text{C}$ .
- (4) Light source is an unfiltered tungsten bulb operating at  $CT = 2870\text{ K}$  or equivalent infrared source.

## Typical Performance Curves

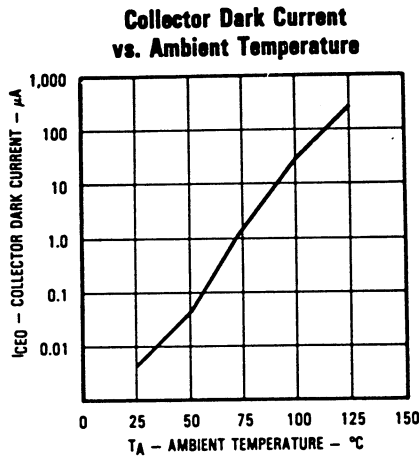
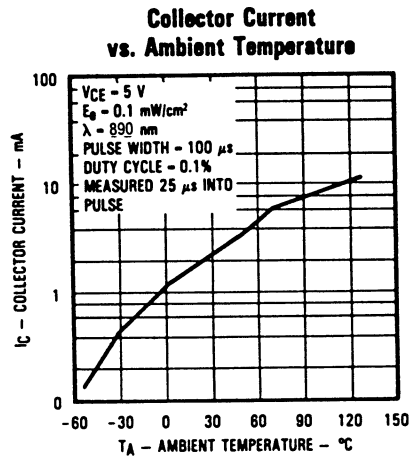
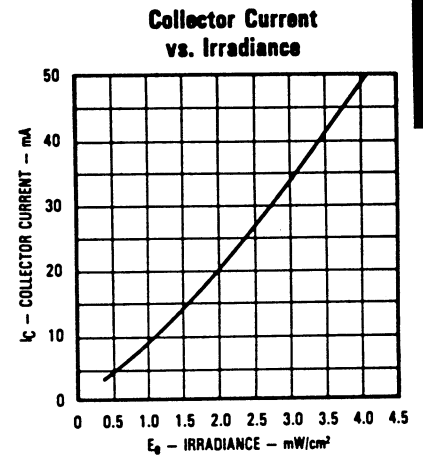
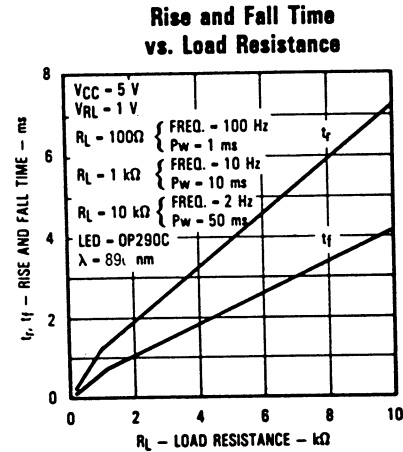
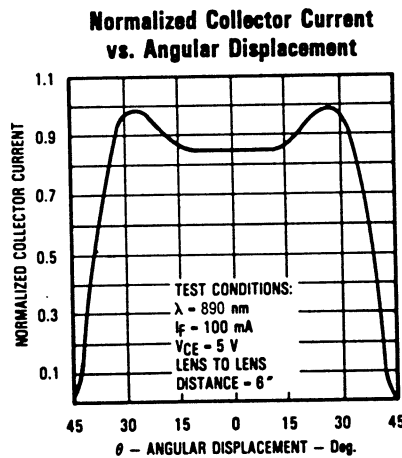


# OP830WSL

Electrical Characteristics ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

| SYMBOL              | PARAMETER                            | MIN | TYP | MAX  | UNITS         | TEST CONDITIONS                                                   |
|---------------------|--------------------------------------|-----|-----|------|---------------|-------------------------------------------------------------------|
| $I_{C(ON)}^{(3)}$   | On-State Collector Current           | 4   |     |      | mA            | $V_{CE} = 5\text{ V}$ , $E_e = 0.5\text{ mW/cm}^2$ <sup>(4)</sup> |
| $I_{CEO}$           | Collector Dark Current               |     |     | 1.0  | $\mu\text{A}$ | $V_{CE} = 10\text{ V}$                                            |
| $V_{(BR)CEO}$       | Collector-Emitter Breakdown Voltage  | 15  |     |      | V             | $I_C = 100\text{ }\mu\text{A}$                                    |
| $V_{(BR)ECO}$       | Emitter-Collector Breakdown Voltage  | 5.0 |     |      | V             | $I_E = 100\text{ }\mu\text{A}$                                    |
| $V_{CE(SAT)}^{(3)}$ | Collector-Emitter Saturation Voltage |     |     | 1.20 | V             | $I_C = 1.0\text{ mA}$ , $E_e = 0.5\text{ mW/cm}^2$ <sup>(4)</sup> |

## Typical Performance Curves



## Switching Time Test Circuit

